**Erratum: Signature of Hanle precession in trilayer MoS₂: Theory and experiment
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Because of uncertainty in the current actually injected inside the MoS₂ trilayer and the procedure used for correcting the background Ohmic resistance contribution, the nonlocal Hanle resistances presented in Figs. 6 and 7 and in Table I of Appendix B are not correct. These cannot be used for making comparison with theory and therefore the related discussion is not relevant. The insertion of a tunnel barrier layer (such as MgO) is essential for injecting spin-polarized carriers in the PLD-grown MoS₂ samples.

Correction: An invalid version of the Erratum was processed and the content has now been fixed.